

TANTALUM SPUTTERING TARGET, AND PRODUCTION METHOD THEREFOR

ABSTRACT

5 Provided is a tantalum sputtering target, which includes an area ratio of
crystal grains of which a {111} plane is oriented in a direction normal to a rolling
surface (ND) is 35% or more when the ND, which is a cross section orthogonal to a
sputtering surface of a target, is observed via Electron Backscatter Diffraction Pattern
method. The object of the present invention is to provide a tantalum sputtering target
10 in which a sputtered material can be uniformly deposited on a wafer surface under
high-power sputtering conditions by increasing the straightness of the sputtered
material. By using this kind of tantalum target for sputter-deposition, it is possible to
improve the film thickness uniformity and the throughput of deposition even for fine
wiring.

15 Elected Figure: FIG. 3